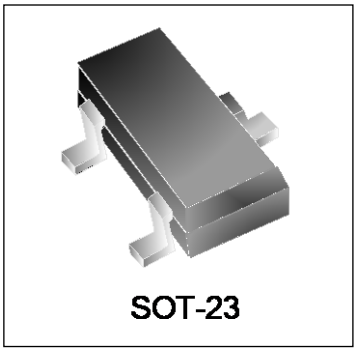
WT2222A

NPN Silicon Transistor



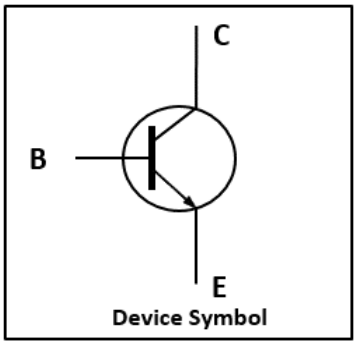
Features

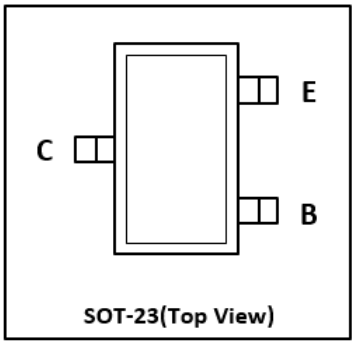
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (WT2907A)

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration





Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	75	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W

Electrical Characteristics (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	75	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	6	-	-	V
Collector Cut-Off Current	I_{CBO}	V_{CB} = 60V, I_E = 0	-	-	10	nA
Collector Cut-Off Current	I_{CEX}	V_{CE} = 30V, $V_{EB(off)}$ = -3V	-	-	10	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB} = 3V, I_C = 0	-	-	100	nA
DC Current Gain	$h_{FE(1)}$	V_{CE} = 5V, I_C = 1mA	200	-	300	-
	$h_{FE(2)}$	V_{CE} = 10V, I_C = 150mA	100	-	-	-
	$h_{FE(3)}$	V_{CE} = 10V, I_C = 0.1mA	40	-	-	-
	$h_{FE(4)}$	V_{CE} = 10V, I_C = 500mA	42	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	-	-	1	V
		I_C = 150mA, I_B = 15mA	-	-	0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 500mA, I_B = 50mA	-	-	2.0	V
		I_C = 150mA, I_B = 15mA	-	-	1.2	V
Transition Frequency	f_T	V_{CE}=20V, I_C=20mA, f=100MHz	300	-	-	MHz
Delay Time	t_d	V_{CC} = 30V, $V_{BE(off)}$ = -0.5V, I_C = 150mA, I_{B1} = 15mA	-	-	10	ns
Rise Time	t_r		-	-	25	ns
Storage Time	t_s	V_{CC} = 30V, I_C = 150mA I_{B1} = -I_{B2} = 15mA	-	-	225	ns
Fall Time	t_f		-	-	60	ns

Typical Characteristics

Figure 1.Static Characteristics

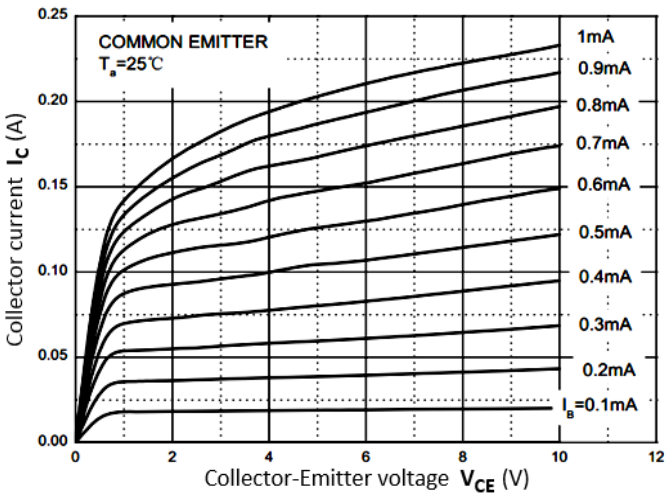


Figure 2. h_{FE} vs. I_C

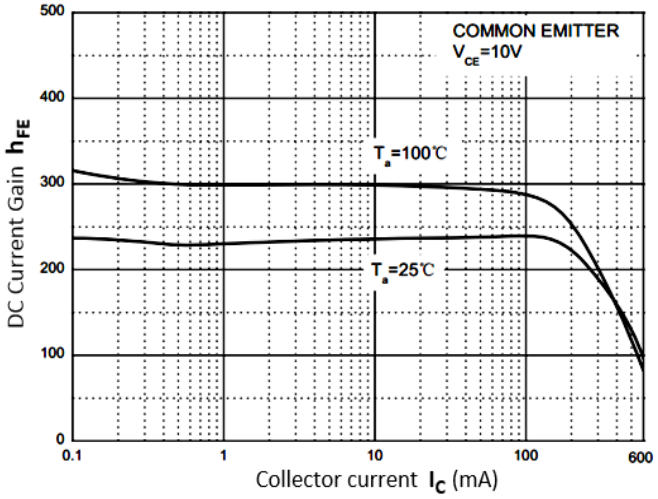


Figure 3. $V_{CE(sat)}$ vs. I_C

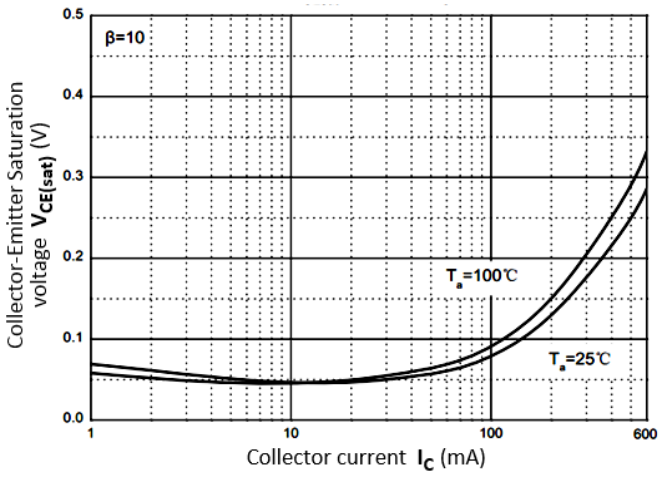


Figure 4. $V_{BE(sat)}$ vs. I_C

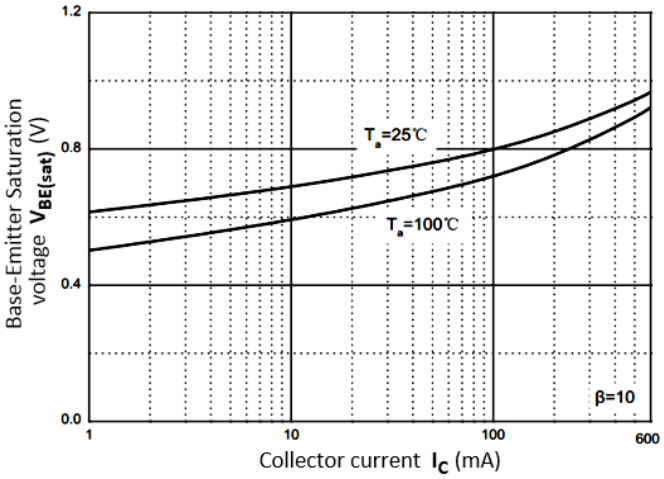


Figure 5. I_C vs. V_{BE}

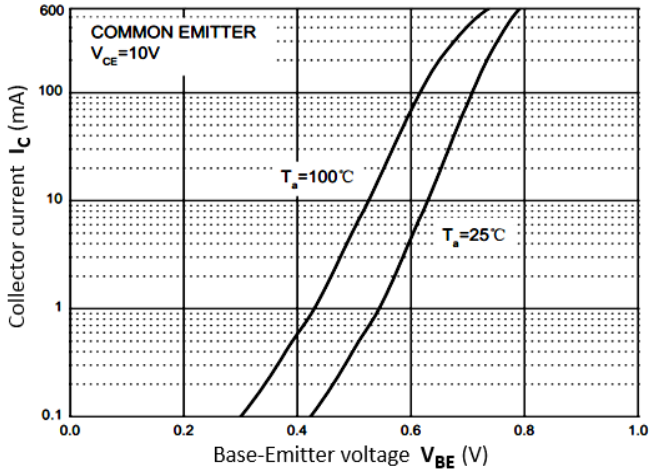


Figure 6. C_{ob} / C_{ib} vs. V_{CB} / V_{EB}

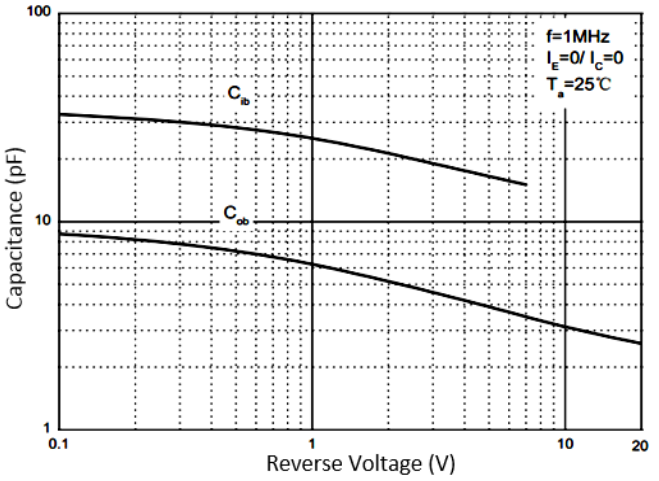


Figure 7. f_T vs. I_C

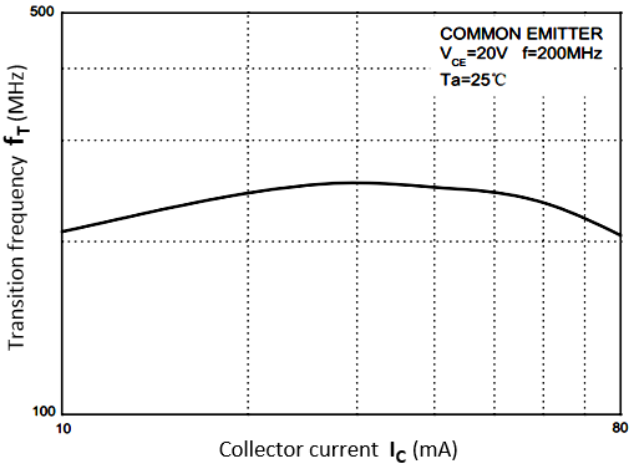
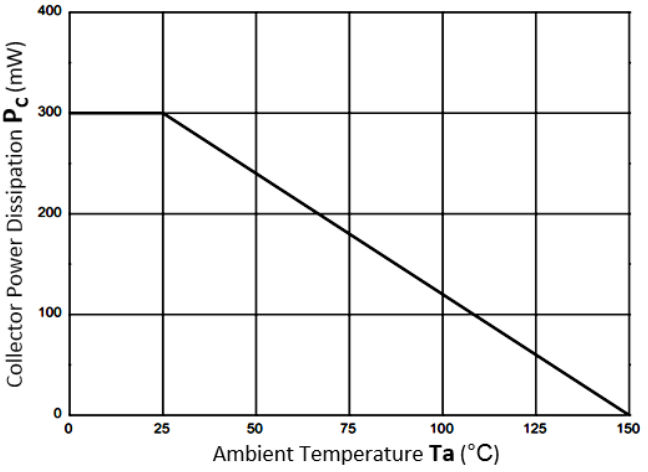
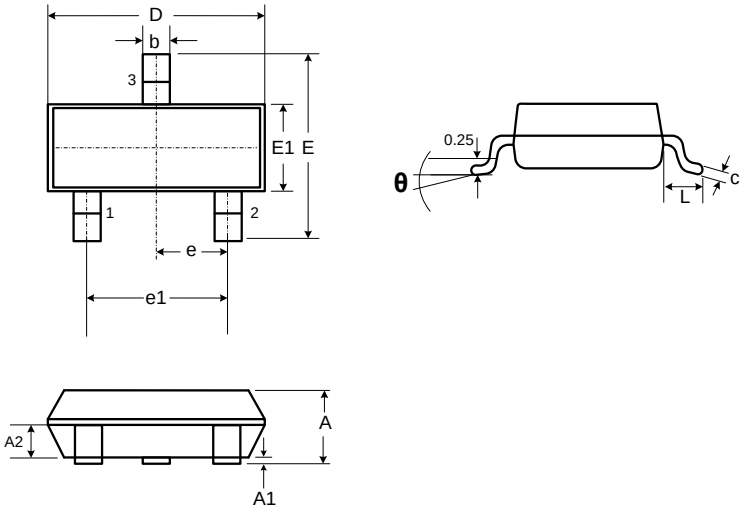


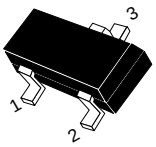
Figure 8. P_C vs. T_a



Outline Drawing – SOT-23

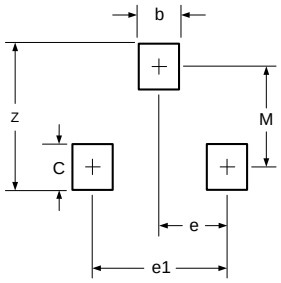
PACKAGE OUTLINE





SOT-23

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
A2	0.60	0.70	0.0236	0.0275
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 BSC	
e1	1.80	2.00	0.071	0.079
L	0.30	0.50	0.012	0.020
θ	0	8°	0	8°



DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.0795	2.02
C	0.0315	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.9 BSC
b	0.0315	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WT2222A
Marking Code	1P

Package Information

Qty：3k/Reel

CONTACT INFORMATION.

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